

ST13003DN

High voltage fast-switching NPN power transistor

Preliminary data

Features

- High voltage capability
- Low spread of dynamic parameters
- Very high switching speed
- Integrated free-wheeling diode

Application

■ Compact fluorescent lamps (CFLs)

Description

The device is manufactured using high voltage multi epitaxial planar technology for high switching speeds and high voltage capability. It uses a cellular emitter structure with planar edge termination to enhance switching speeds while maintaining the wide RBSOA.

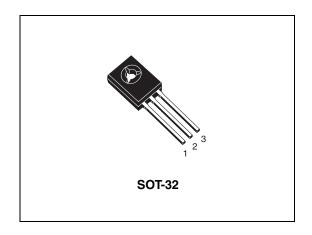


Figure 1. Internal schematic diagram

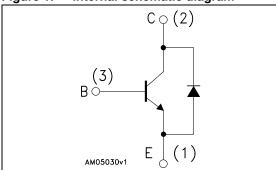


Table 1. Device summary

Order code	Marking	Package	Packaging
ST13003DN	13003DN	SOT-32	BAG

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Electrical ratings ST13003DN

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit	
V _{CES}	Collector-emitter voltage (V _{BE} = 0)	700	V	
V _{CEO}	Collector-emitter voltage (I _B = 0)	400	V	
V _{EBO}	Collector-base voltage (I _C = 0)	9	V	
Ic	Collector current	1	Α	
I _{CM}	Collector peak current (t _P < 5 ms)	2	Α	
I _B	Base current	0.5	Α	
I _{BM}	Base peak current (t _P < 5 ms)	1	Α	
P _{TOT}	Total dissipation at T _c = 25 °C	20	W	
T _{STG}	Storage temperature	-55 to 150	• °C	
T_J	Max. operating junction temperature	150]	

Table 3. Thermal data

	Symbol	Parameter	Value	Unit
Ī	R _{thJC}	Thermal resistance junction-case	6.25	°C/W

2 Electrical characteristics

 T_{case} = 25 °C; unless otherwise specified.

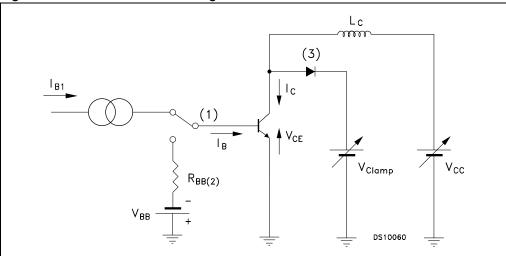
Table 4. Electrical characteristics

Symbol	Parameter	Test condit	tions	Min.	Тур.	Max.	Unit
I _{CES}	Collector cut-off current	V _{CE} = 700 V	T 105 °C			1 5	mA
	(V _{BE} = 0)	$V_{CE} = 700 \text{ V}$	1C = 125 °C			5	mA
I _{EBO}	Emitter cut-off current (I _C = 0)	V _{EB} = 9 V				1	mA
V _{CEO(sus)}	Collector-emitter sustaining voltage (I _B = 0)	I _C = 10 mA		400			V
V _{CE(sat)} (1)	Collector-emitter saturation	$I_C = 0.5 A I_B$	= 125 mA			0.7	V
VCE(sat)	voltage	$I_C = 1 A I_B$	= 330 mA			1.2	V
v (1)	Base-emitter saturation	$I_C = 0.5 A I_B$	= 125 mA			1.2	V
V _{BE(sat)} (1)	voltage	$I_C = 1 A I_B$	= 330 mA			1.3	V
h	DC current gain	$I_C = 0.5 \text{ A}, V_C$	_{CE} = 2 V	6		18	
h _{FE}	DC current gain	$I_C = 1 A$ V_C	_{CE} = 10 V	5		15	
	Inductive Load	I _C = 0.4 A V _{clamp}	= 300 V				
t _s	Storage time	$I_{B(on)} = -I_{B(off)} = 80$			2.5		μs
t _f	Fall time	$V_{BB(off)} = -5 \text{ V}$	Figure 2		180		ns
V _F	Diode forward voltage	I _F = 350 mA			1.5		V

^{1.} Pulse test: pulse duration $\leq 300~\mu s,$ duty cycle $\leq 2~\%$

2.1 Test circuit

Figure 2. Inductive load switching test circuit



- 1. Fast electronic switch
- 2. Non-inductive resistor
- 3. Fast recovery rectifier

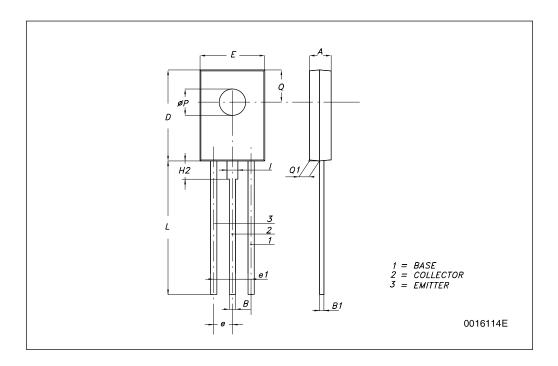
3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of $\mathsf{ECOPACK}^{\mathbb{B}}$ packages, depending on their level of environmental compliance. $\mathsf{ECOPACK}^{\mathbb{B}}$ specifications, grade definitions and product status are available at: $\mathit{www.st.com}$. $\mathsf{ECOPACK}^{\mathbb{B}}$ is an ST trademark.

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SOT-32 (T	O-126)	MECHAN	ICAL	DATA
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DIM.	mm.				
	MIN.	TYP	MAX.		
Α	2.4		2.9		
В	0.64		0.88		
B1	0.39		0.63		
D	10.5		11.05		
E	7.4		7.8		
е	2.04	2.29	2.54		
e1	4.07	4.58	5.08		
L	15.3		16		
Р	2.9		3.2		
Q		3.8			
Q1	1		1.52		
H2		2.15			
ı		1.27			



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ST13003DN Revision history

4 Revision history

Table 5. Document revision history

Date	Revision	Changes
25-Feb-2010	1	First release.

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